

2SA2079

Silicon PNP epitaxial planar type

For general amplification

Complementary to 2SC5848

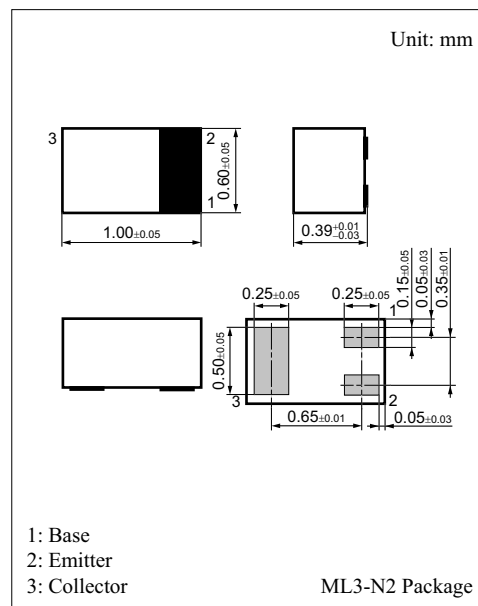
■ Features

- High forward current transfer ratio h_{FE}
- Suitable for high-density mounting and downsizing of the equipment for ultraminiature leadless package

Package: 0.6 mm × 1.0 mm (height 0.39 mm)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	−45	V
Collector-emitter voltage (Base open)	V_{CEO}	−45	V
Emitter-base voltage (Collector open)	V_{EBO}	−7	V
Collector current	I_C	−100	mA
Peak collector current	I_{CP}	−200	mA
Collector power dissipation	P_C	100	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	−55 to +125	$^\circ\text{C}$

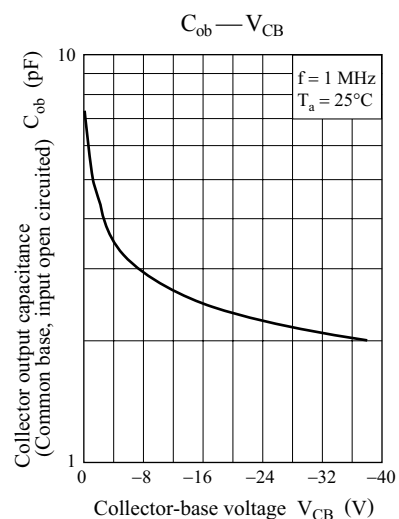
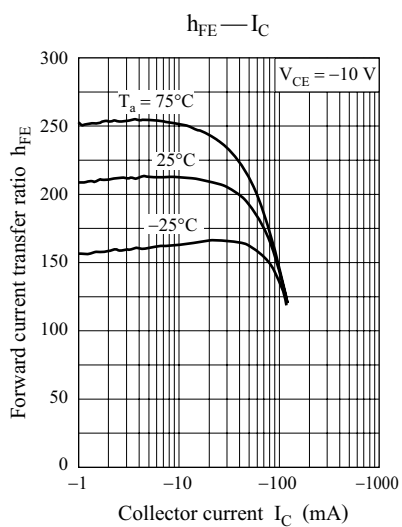
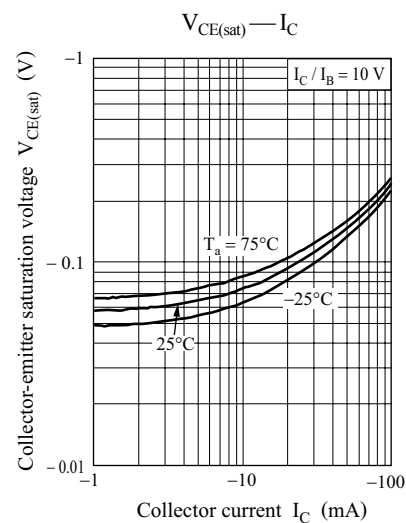
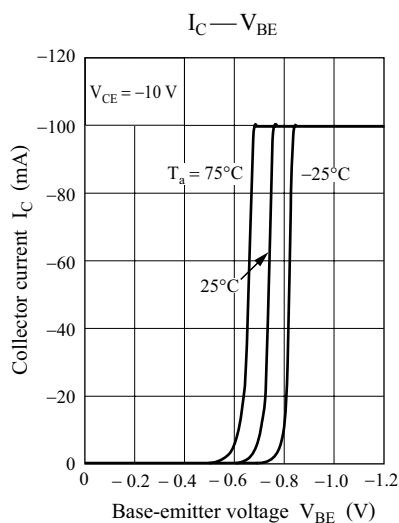
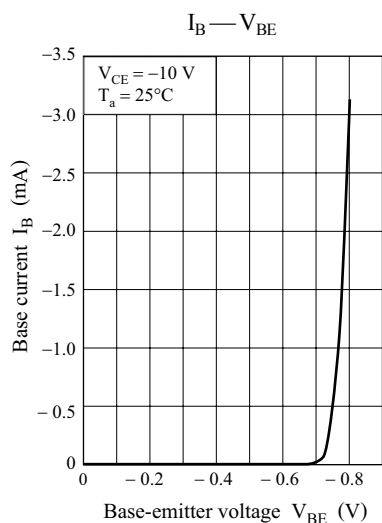
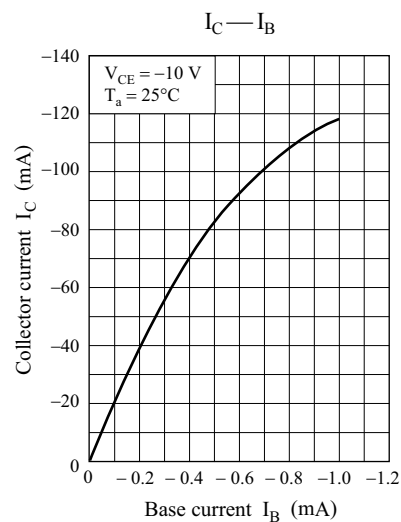
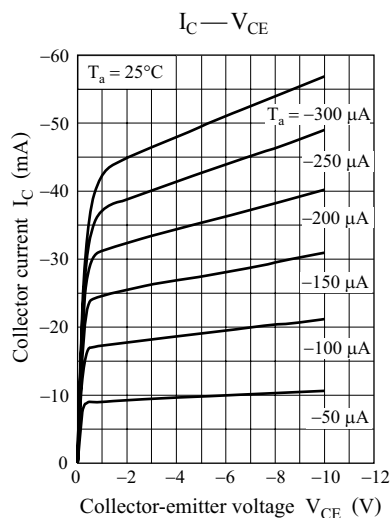
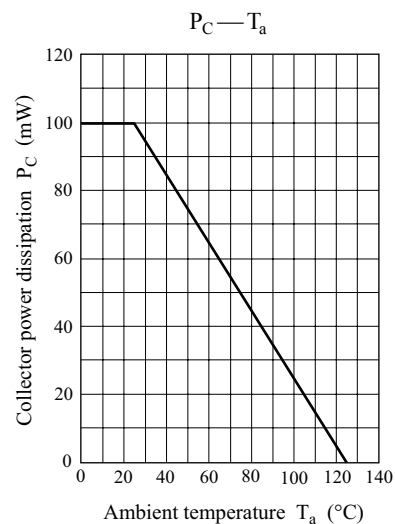


Marking Symbol : 3D

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = -10 \mu\text{A}$, $I_E = 0$	−45			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = -2 \text{ mA}$, $I_B = 0$	−45			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -10 \mu\text{A}$, $I_C = 0$	−7			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -20 \text{ V}$, $I_E = 0$			−0.1	μA
Collector-emitter cut-off current (Base open)	I_{CEO}	$V_{CE} = -10 \text{ V}$, $I_B = 0$			−100	μA
Forward current transfer ratio	h_{FE}	$V_{CE} = -10 \text{ V}$, $I_C = -2 \text{ mA}$	180		390	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100 \text{ mA}$, $I_B = -10 \text{ mA}$		−0.2	−0.5	V
Transition frequency	f_T	$V_{CB} = -10 \text{ V}$, $I_E = 1 \text{ mA}$, $f = 200 \text{ MHz}$		80		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = -10 \text{ V}$, $I_E = 0$, $f = 1 \text{ MHz}$		2.2		pF

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.



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